

FIG. 2

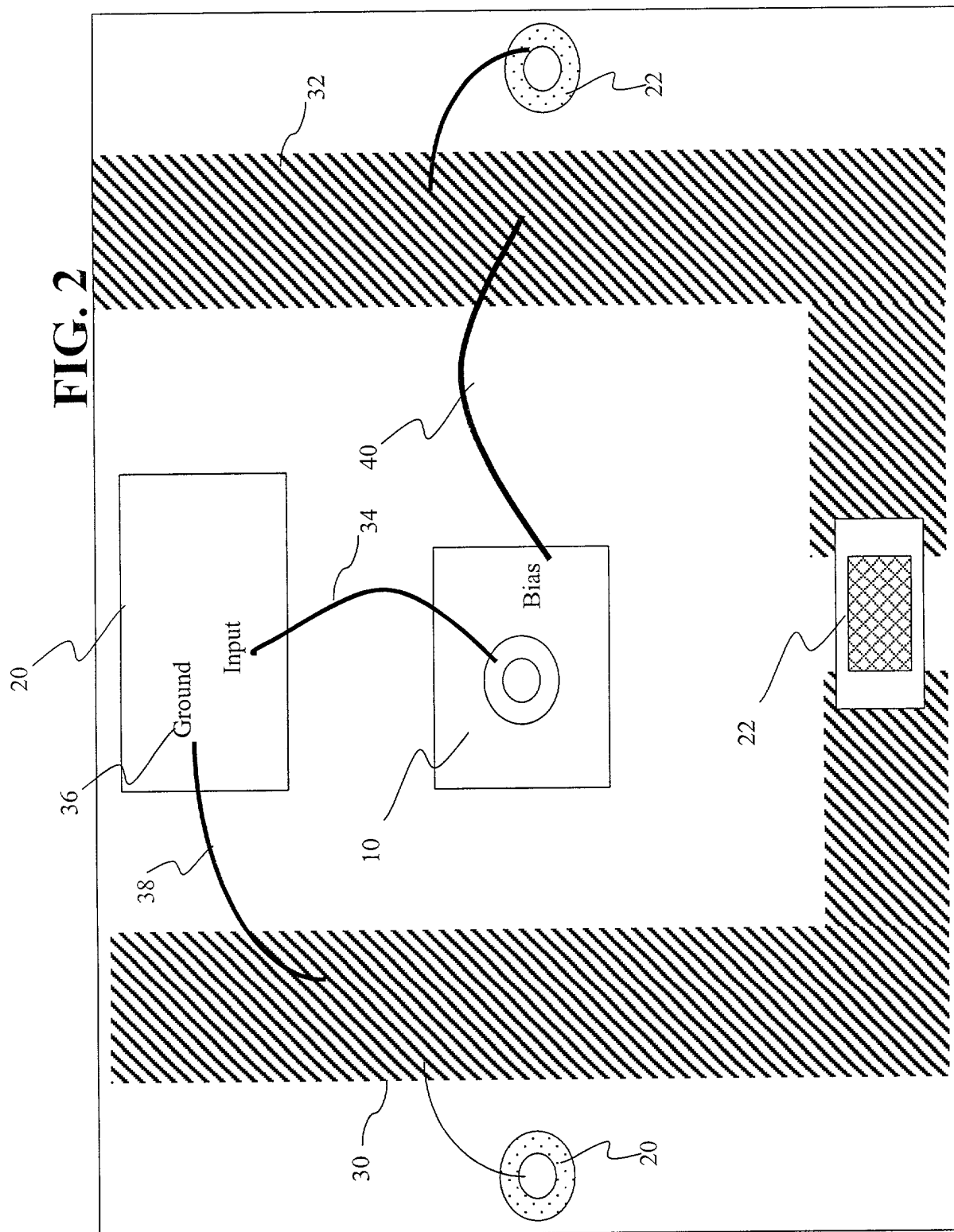


FIG. 2

FIG. 3

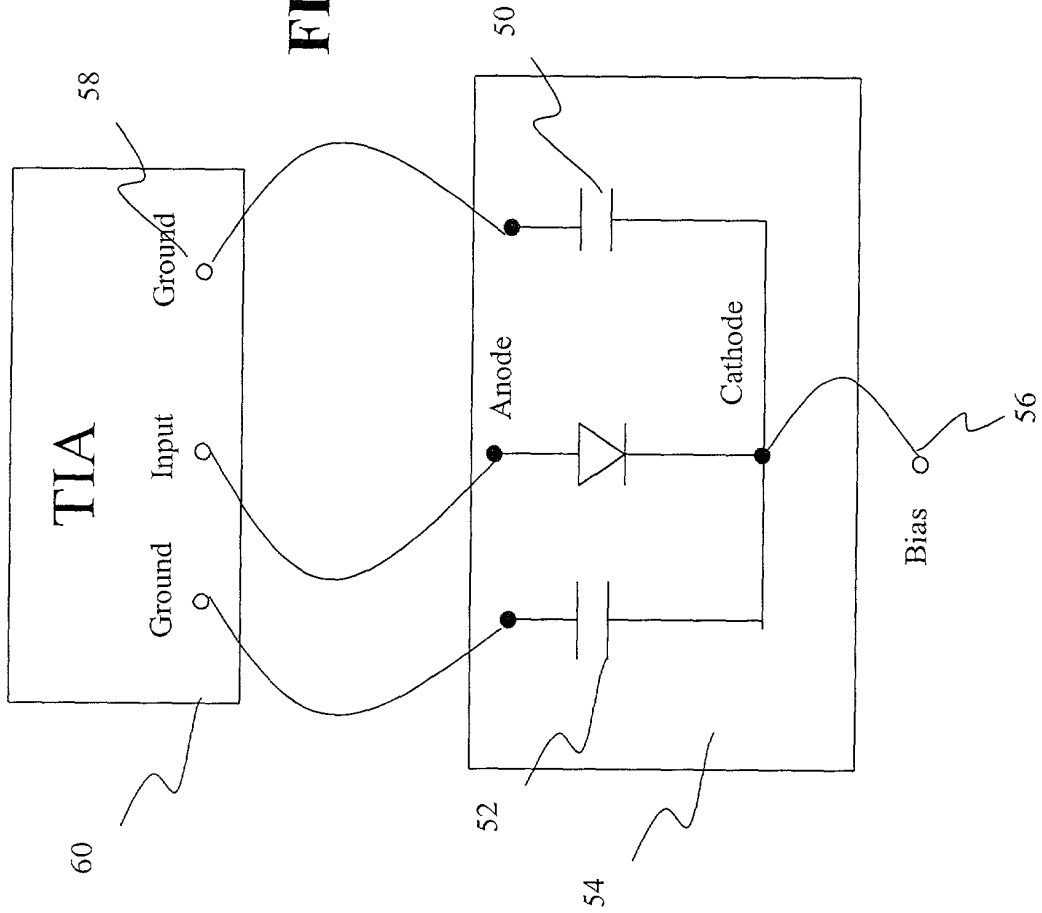
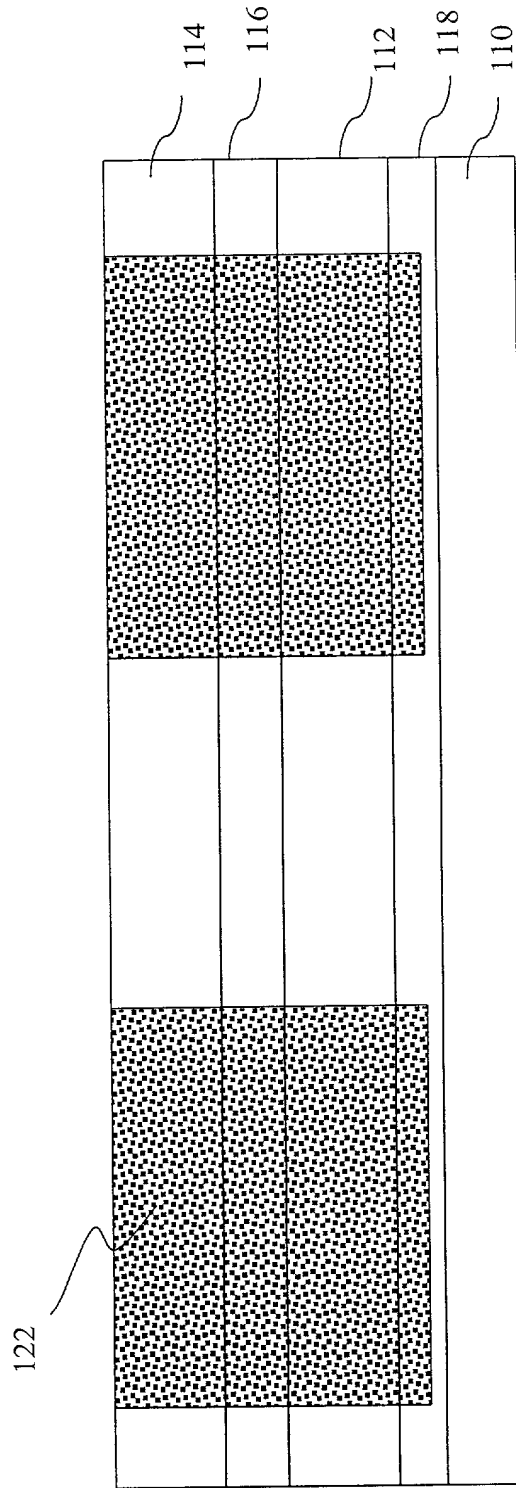


FIG. 4



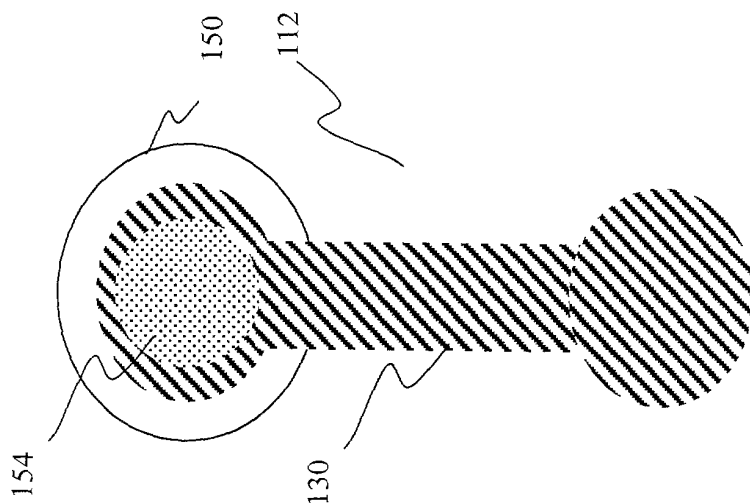
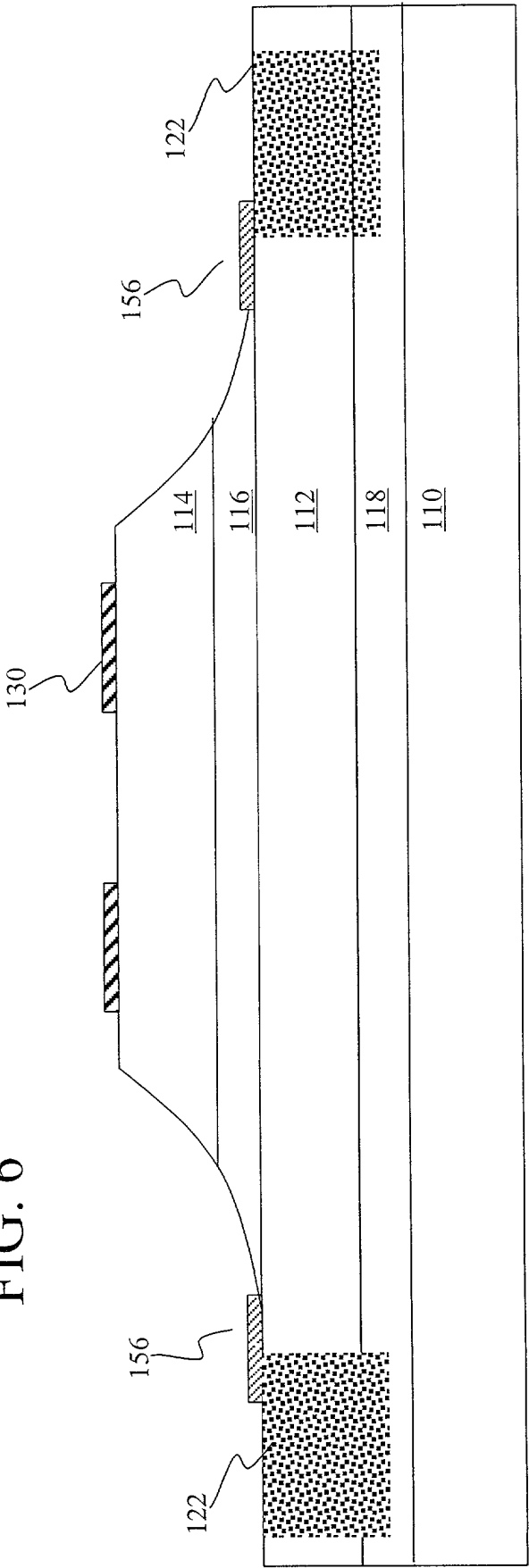


FIG. 5

FIG. 5 is a cross-sectional diagram of a detector structure.

FIG. 6



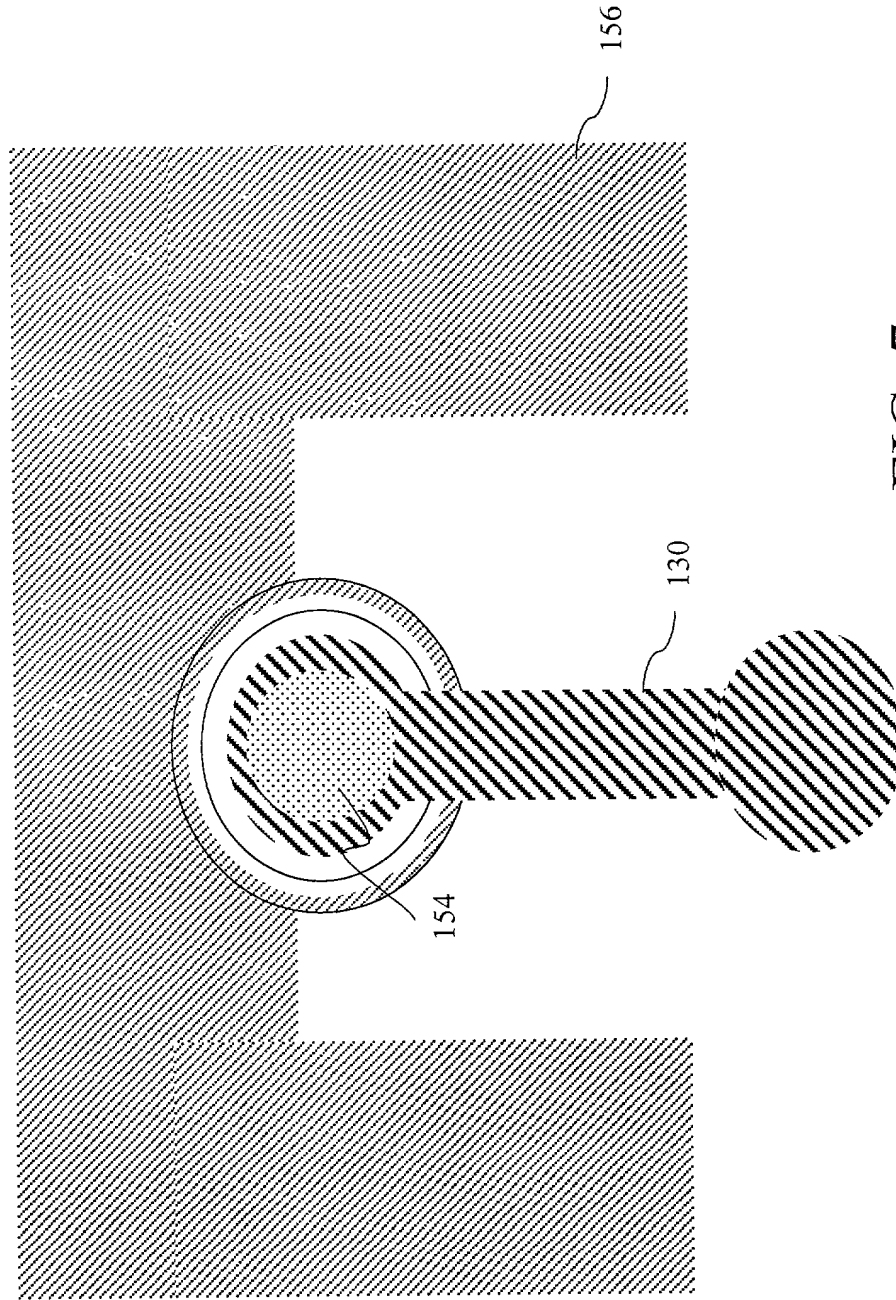


FIG. 7

FIG. 7

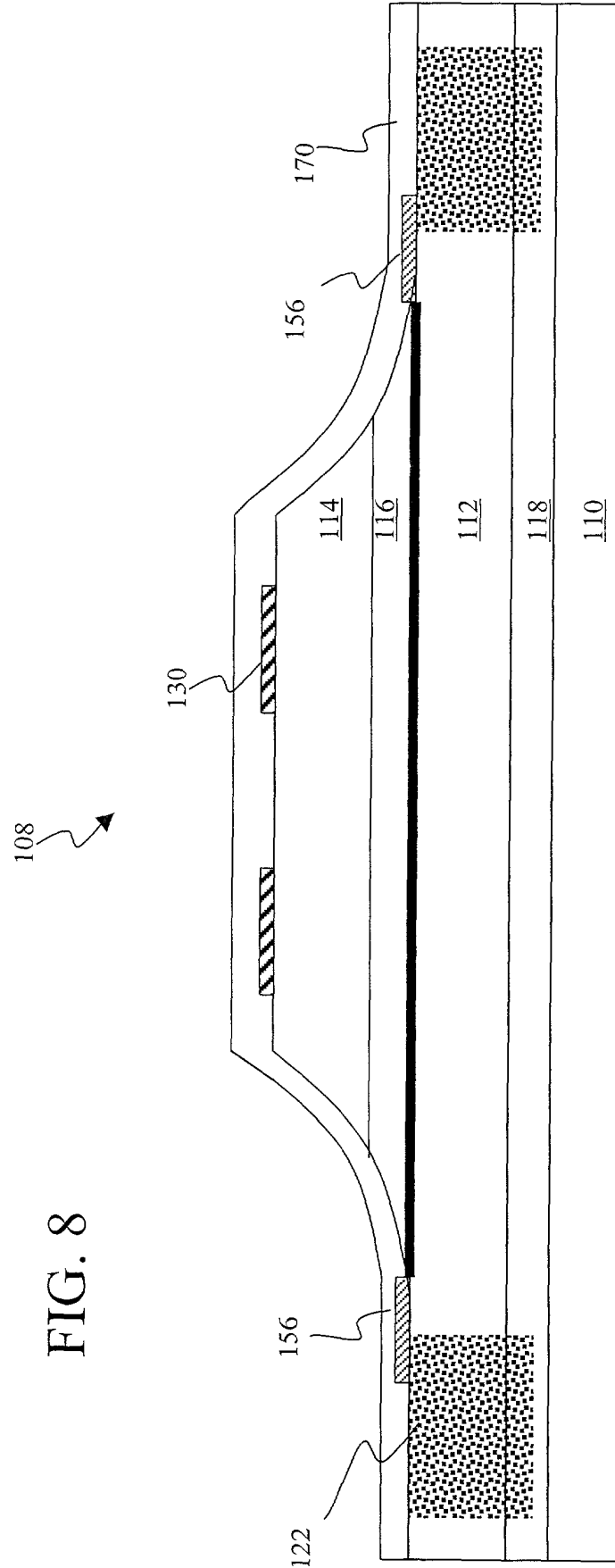




FIG. 9

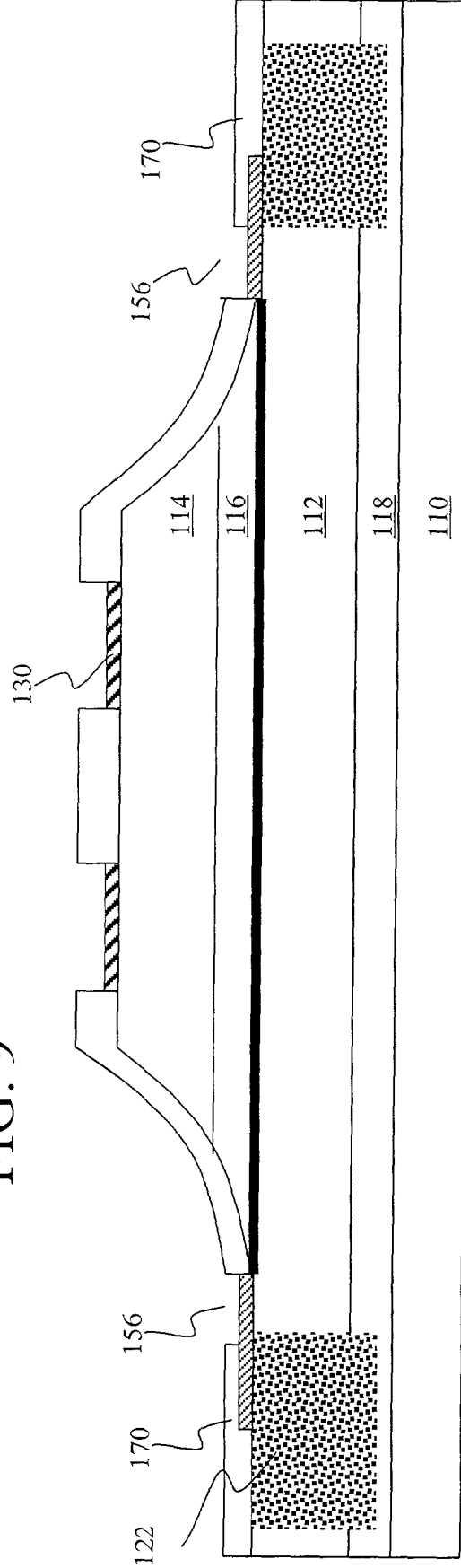
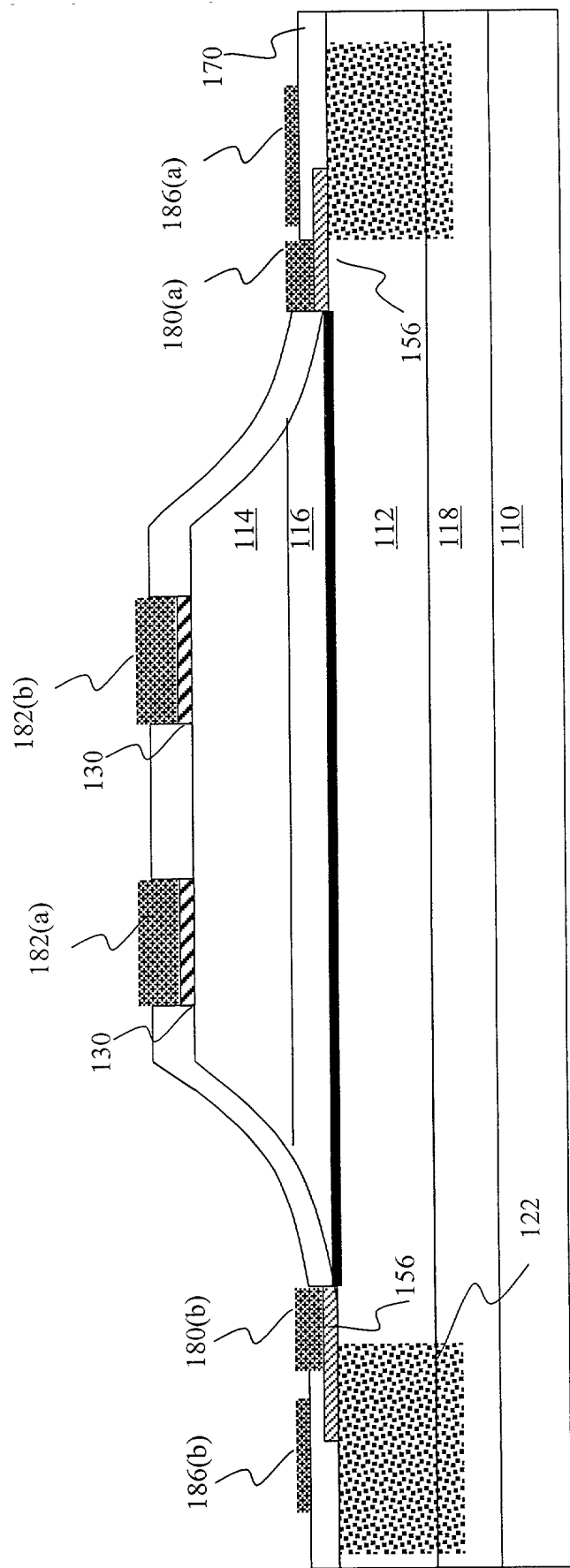


FIG. 10



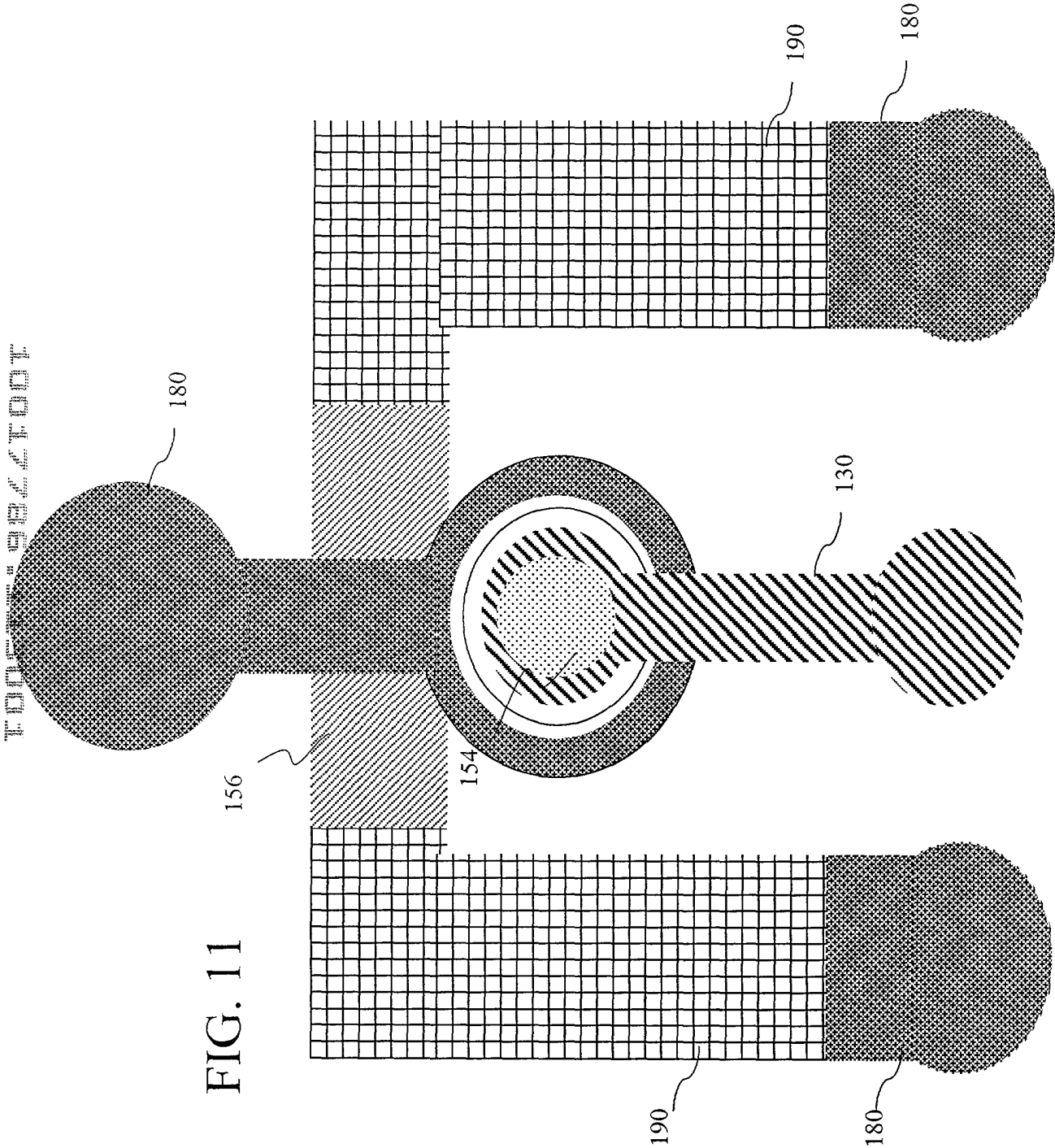
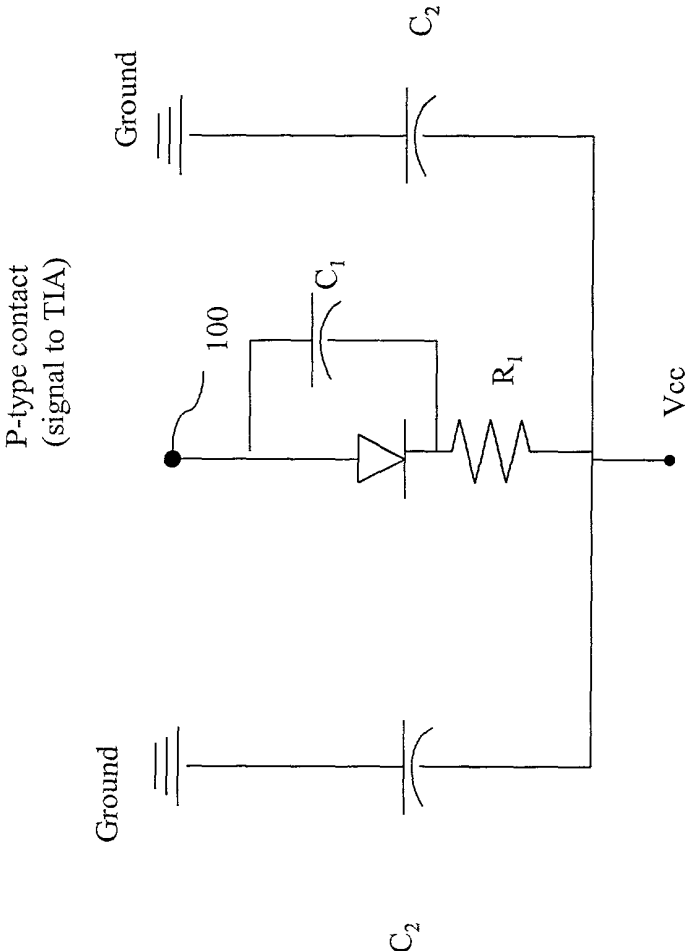


FIG. 12

FIG. 12



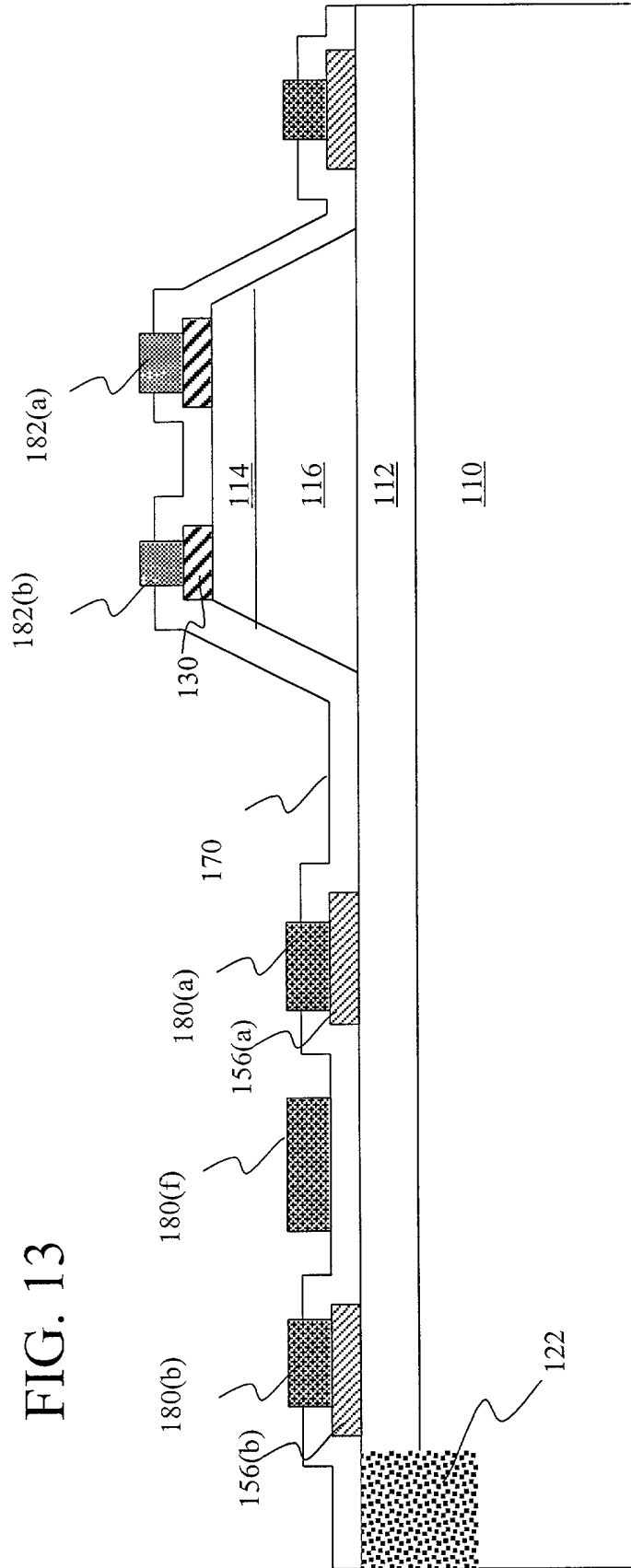


FIG. 13

FIG. 14

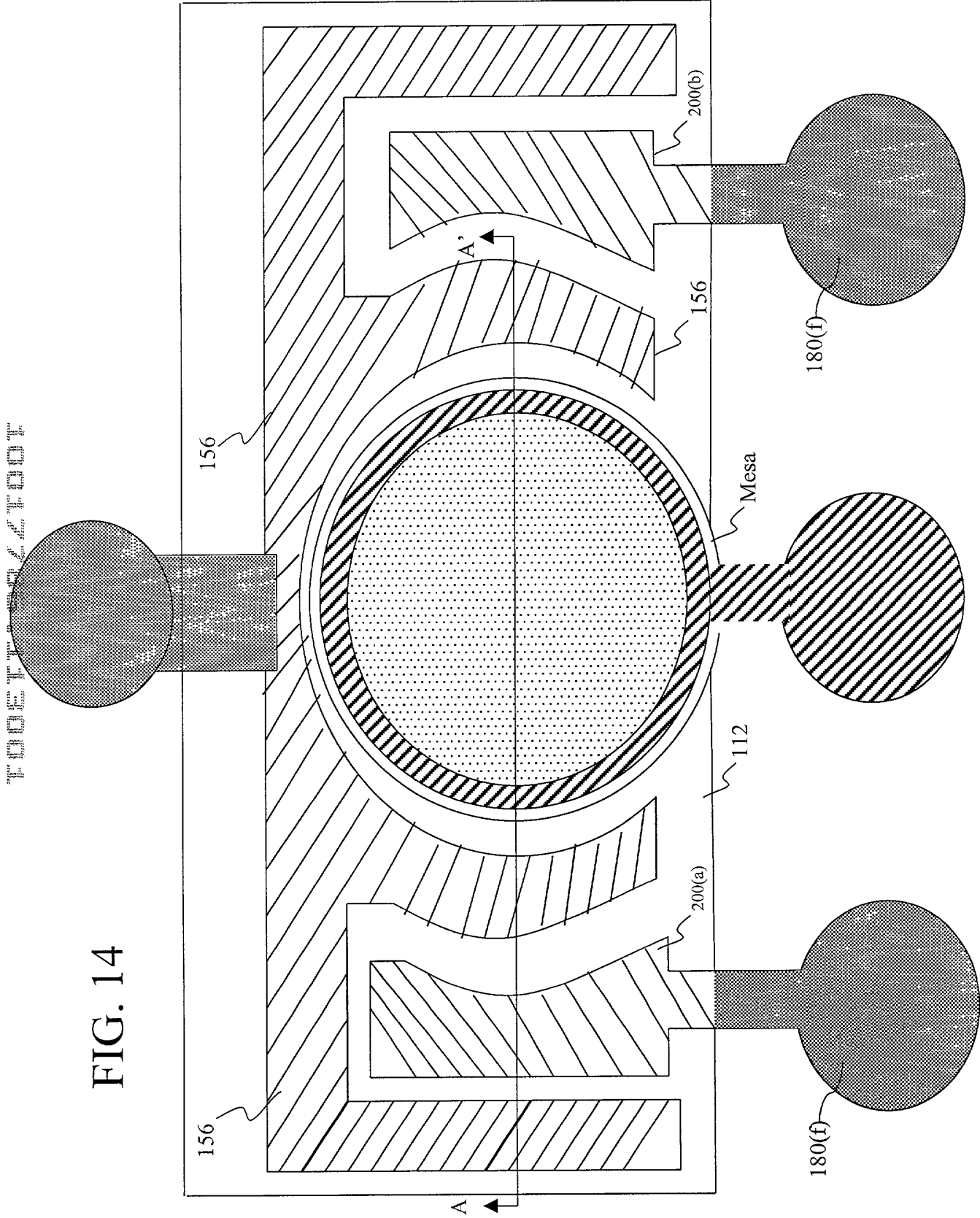




FIG. 16

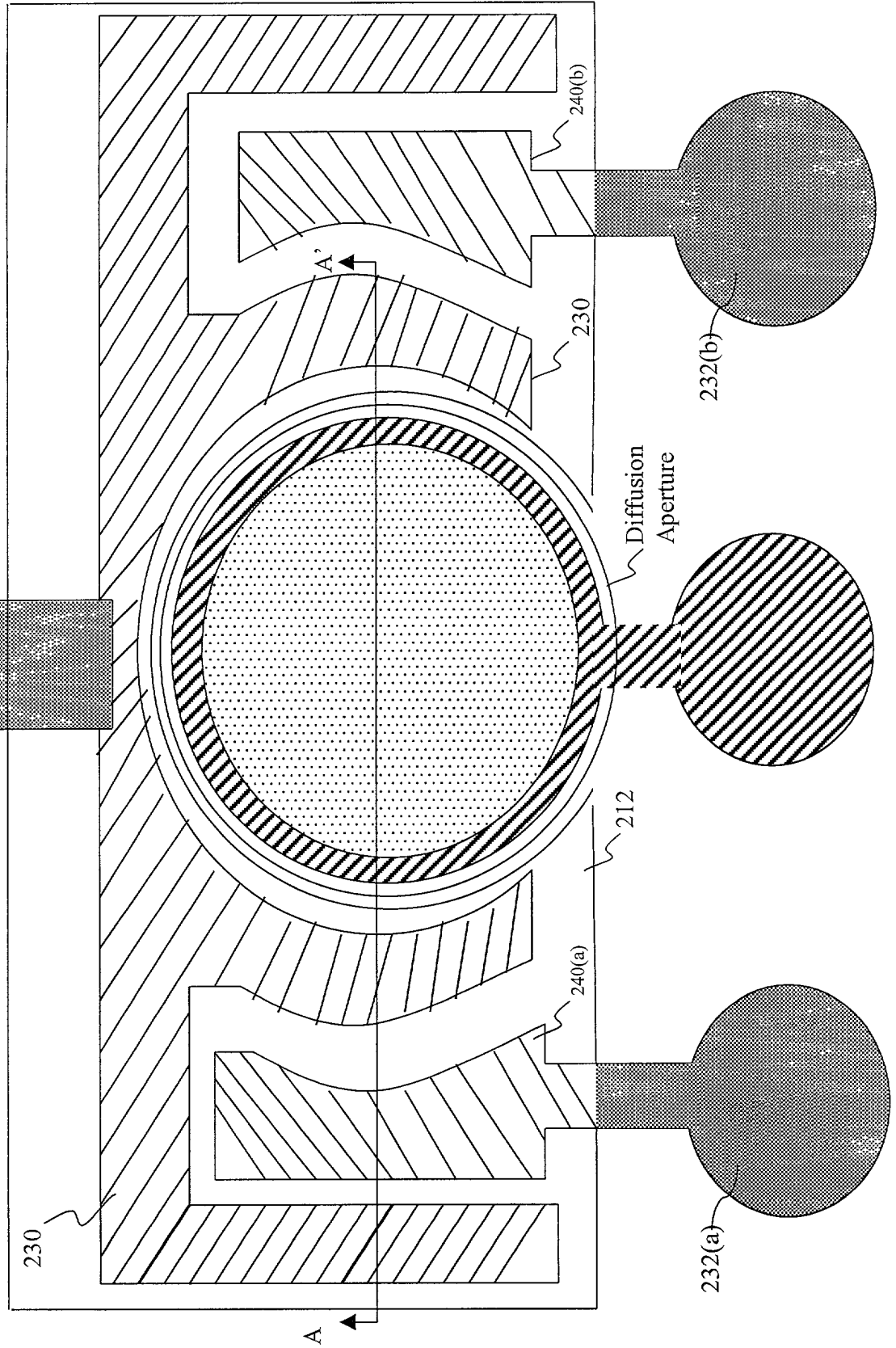






FIG. 18

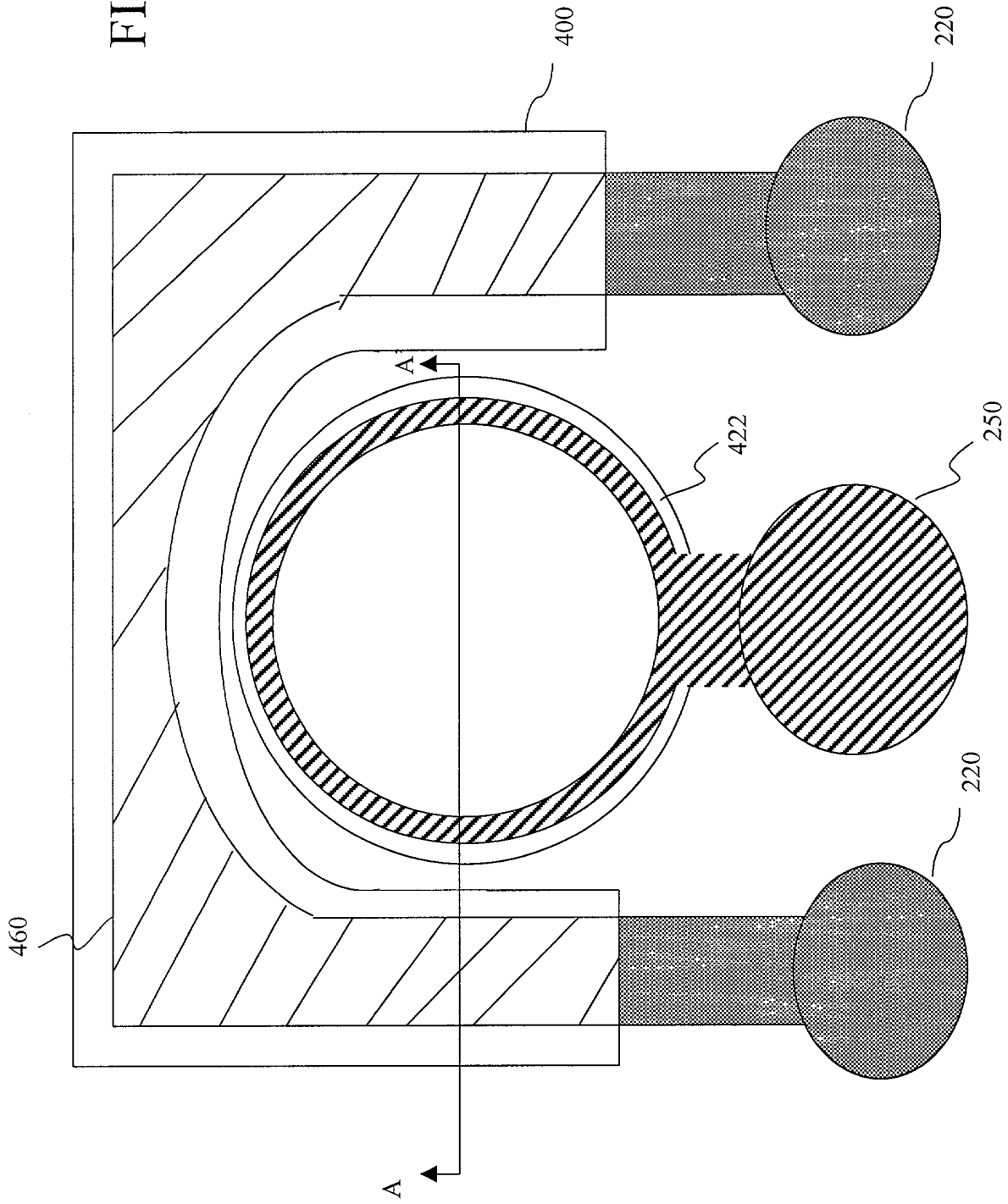




Fig. 1 is a cross-sectional view of a semiconductor device 500. The device includes a substrate 500 with a layer 510. A gate stack 560(a) is formed on the surface of the substrate 500. The gate stack 560(a) includes a gate dielectric 560(b) and a gate electrode 560(c). A channel region 570 is defined by the gate stack 560(a). Source and drain regions 580(a) and 580(b) are formed in the substrate 500. A contact layer 530 and a contact pad 520 are formed on the source and drain regions 580(a) and 580(b).

FOOT DETECTOR

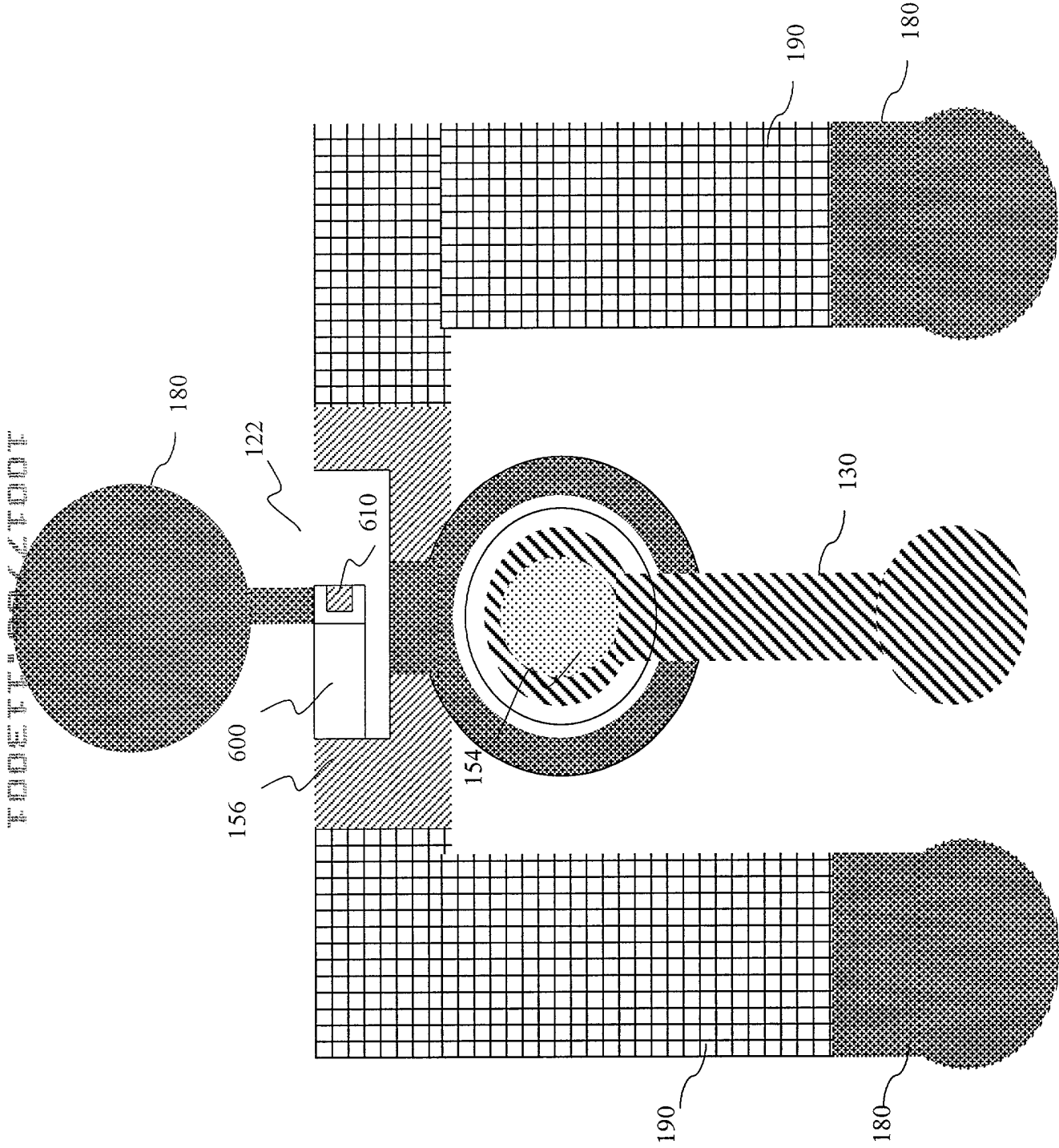
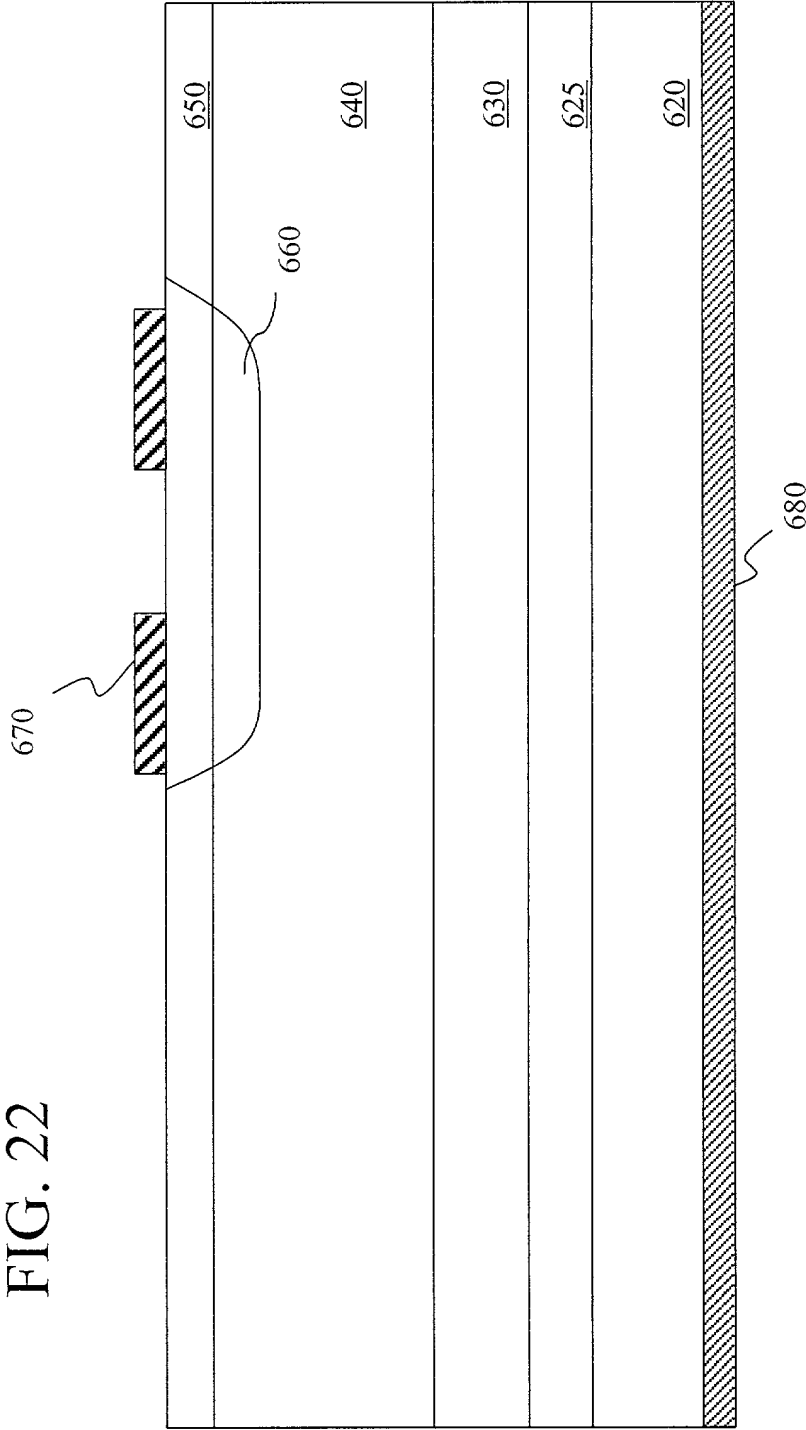


FIG. 21



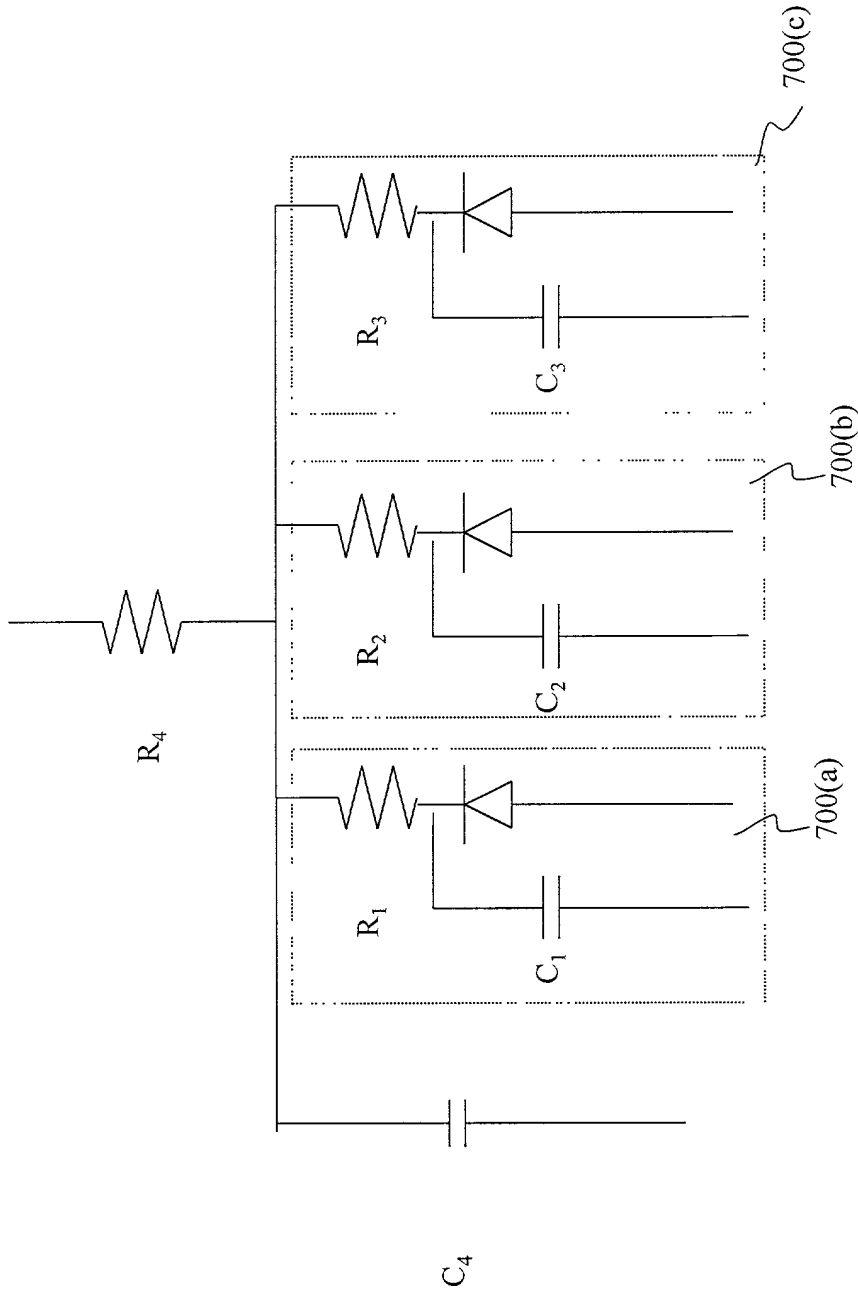


FIG. 23

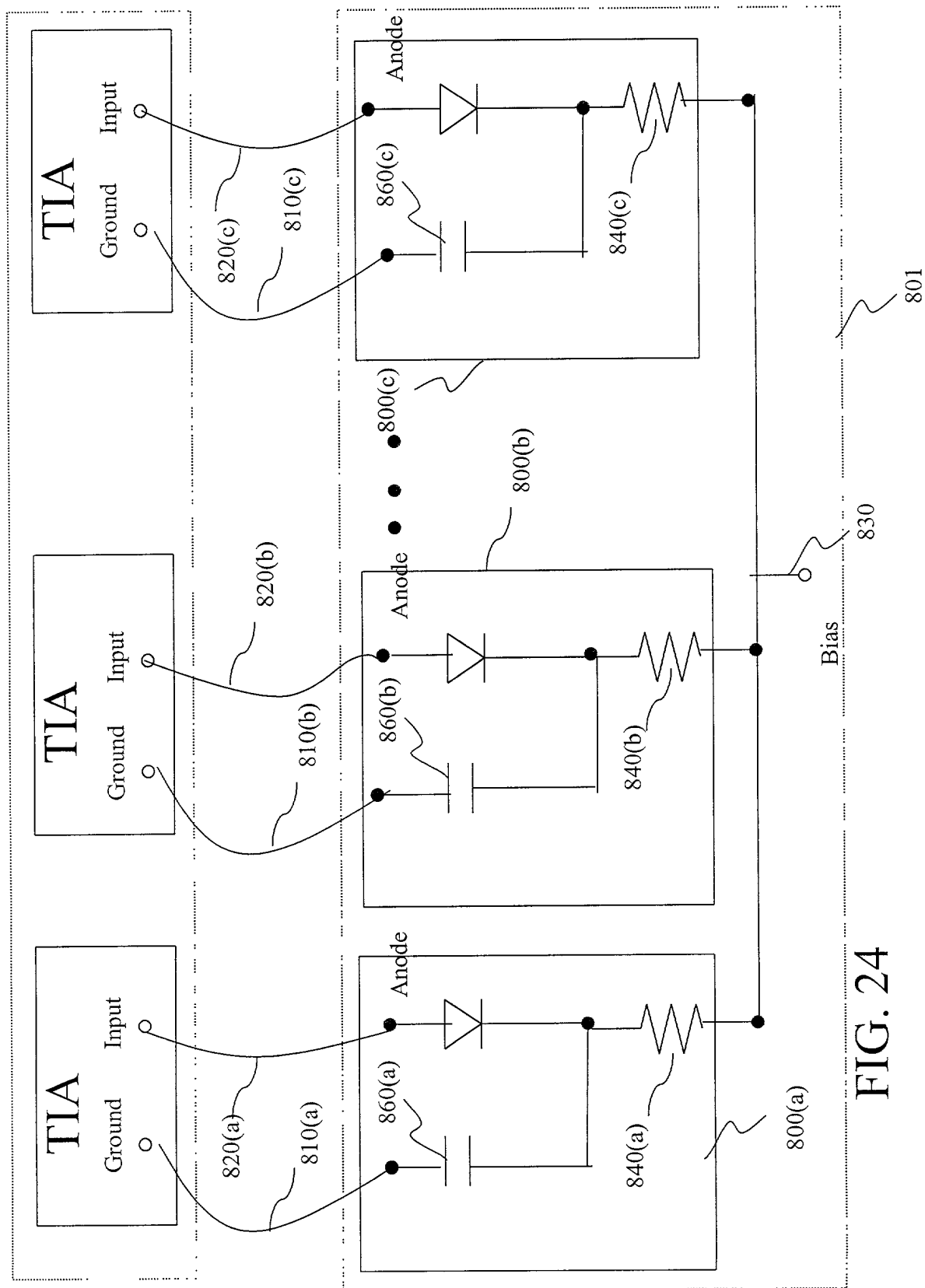


FIG. 24



FIG. 25

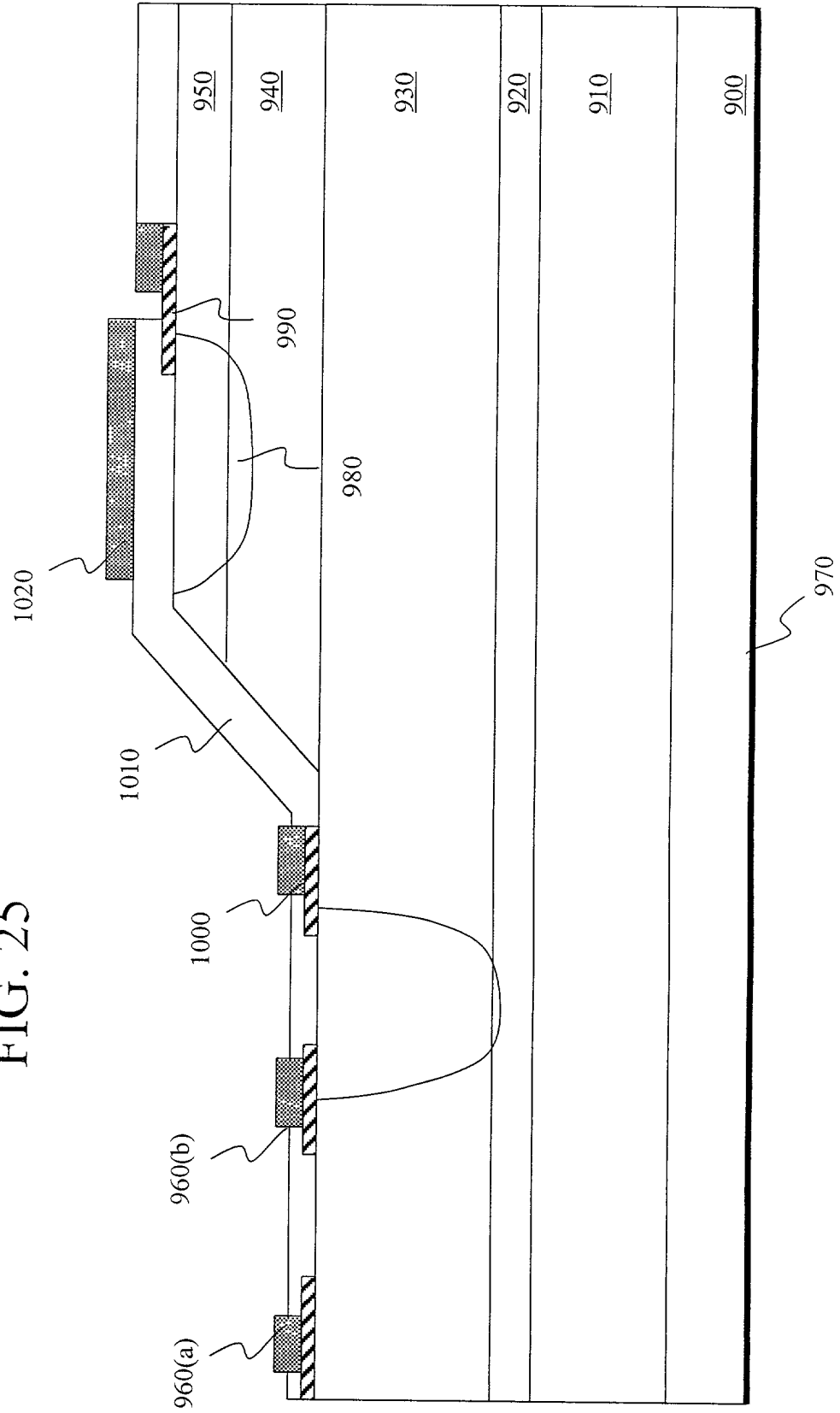


FIG. 26

